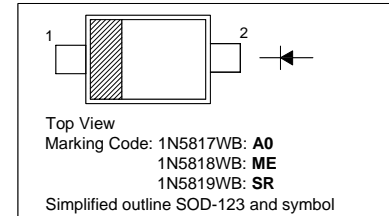


# 1N5817WB-1N5819WB

## 1 A SURFACE MOUNT SCHOTTKY BARRIER DIODE

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

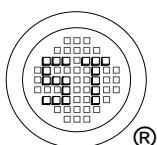


### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	1N5817WB	20
		1N5818WB	30
		1N5819WB	40
Average Forward Rectified Current	$I_O$	1	A
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine-Wave)	$I_{FSM}$	25	A
Power Dissipation	$P_{tot}$	450	mW
Operating Temperature Range	$T_J$	- 55 to + 150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 150	$^\circ\text{C}$

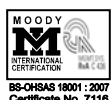
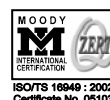
### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1\text{ mA}$	$V_{BR}$	1N5817WB	20	-
		1N5818WB	30	-
		1N5819WB	40	-
Reverse Voltage Leakage Current	$I_R$	at $V_R = 20\text{ V}$ 1N5817WB	-	1
		at $V_R = 30\text{ V}$ 1N5818WB	-	1
		at $V_R = 40\text{ V}$ 1N5819WB	-	1
		at $V_R = 4\text{ V}$ 1N5819WB	-	0.05
		at $V_R = 6\text{ V}$ 1N5819WB	-	0.075
Forward Voltage	$V_F$	at $I_F = 0.1\text{ A}$ 1N5819WB	-	0.45
		at $I_F = 1\text{ A}$ 1N5817WB	-	0.45
		1N5818WB	-	0.55
		1N5819WB	-	0.6
		at $I_F = 3\text{ A}$ 1N5817WB	-	0.75
		1N5818WB	-	0.875
1N5819WB	-	0.9		
Diode Capacitance at $V_R = 4\text{ V}$ , $f = 1\text{ MHz}$	$C_D$	-	120	pF



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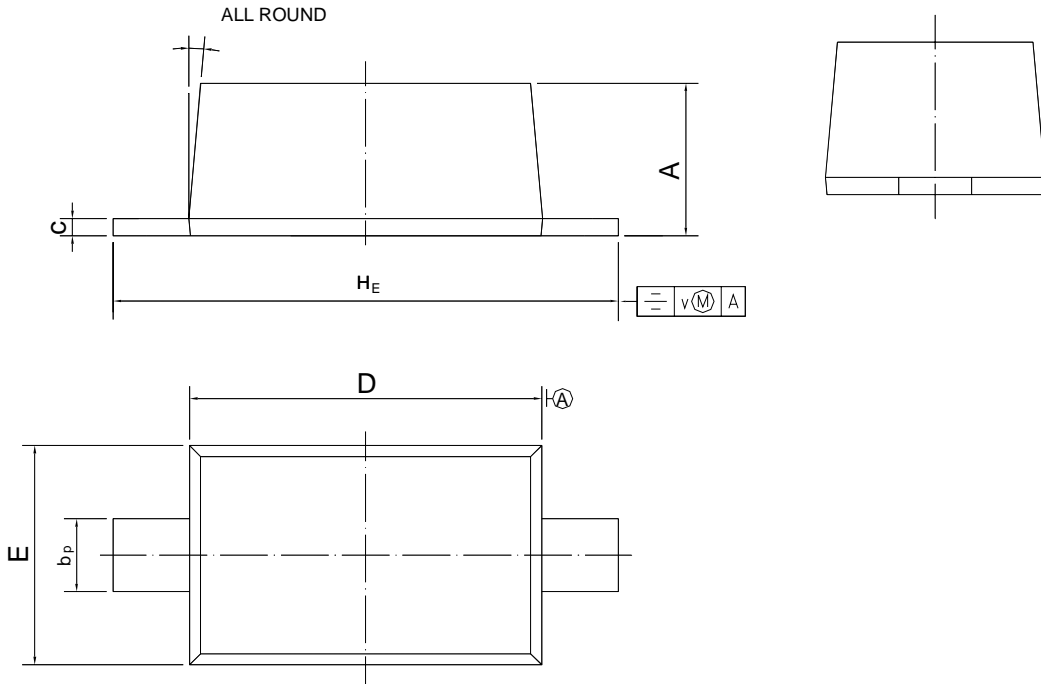
Dated : 20/12/2006

# 1N5817WB-1N5819WB

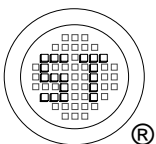
## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b <sub>p</sub>	c	D	E	H <sub>E</sub>	v	
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.9 3.7	0.2	5°



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Dated : 20/12/2006